

FDP10N60NZ / FDPF10N60NZ

N沟道UniFET™ II MOSFET

600 V, 10 A, 750 mΩ

特性

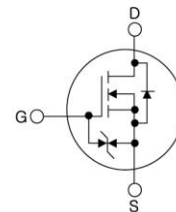
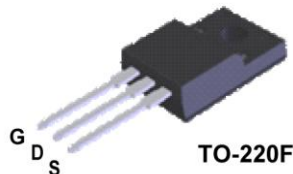
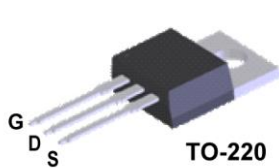
- $R_{DS(on)} = 640 \text{ m}\Omega$ (典型值) @ $V_{GS} = 10 \text{ V}$, $I_D = 5 \text{ A}$
- 低栅极电荷 (典型值 23 nC)
- 低 C_{rss} (典型值 10 pF)
- 100%经过雪崩测试
- 改善的dv/dt处理能力
- 增强的 ESD 能力
- 符合 RoHS 标准

说明

UniFET™ II MOSFET是飞兆半导体的高压MOSFET系列产品, 基于平面条形技术和DMOS技术。该先进MOSFET系列产品在平面 MOSFET 产品中具有最小的通态电阻, 还可提供卓越的开关性能和更高的雪崩能量强度。此外, 内部的栅源 ESD 二极管使 UniFET™ II MOSFET 产品可承受超过 2kV 的 HBM静电冲击应力。该器件系列适用于开关电源转换器应用, 如功率因数校正 (PFC)、平板显示器 (FPD) 电视电源、ATX 及灯用电子镇流器。

应用

- LCD/ LED/ PDP TV
- 照明
- 不间断电源



MOSFET最大额定值 $T_c = 25^\circ\text{C}$, 除非另有说明*

符号	参数	FDP10N60NZ	FDPF10N60NZ	单位
V_{DSS}	漏极-源极电压	600		V
V_{GSS}	栅极-源极电压	±25		V
I_D	漏极电流	- 连续 ($T_c = 25^\circ\text{C}$)	10	10*
		- 连续 ($T_c = 100^\circ\text{C}$)	6	6*
I_{DM}	漏极电流 (注 1)	40	40*	A
E_{AS}	单脉冲雪崩能量 (注 2)	550		mJ
I_{AR}	雪崩电流 (注 1)	10		A
E_{AR}	重复雪崩能量 (注 1)	18.5		mJ
dv/dt	二极管恢复dv/dt峰值 (注 3)	10		V/ns
P_D	功耗 ($T_c = 25^\circ\text{C}$)	-	185	38
		- 降低至 25°C 以上	1.5	0.3
T_J T_{STG}	工作和存储温度范围	-55 to +150		$^\circ\text{C}$
T_L	用于焊接的最大引脚温度, 距离外壳1/8", 持续5秒	300		$^\circ\text{C}$

*漏极电流受限于最大结温

热性能

符号	参数	FDP10N60NZ	FDPF10N60NZ	单位
$R_{\theta JC}$	结至外壳热阻最大值	0.68	3.3	$^\circ\text{C}/\text{W}$
$R_{\theta CS}$	外壳与散热体之间的热阻典型值	0.5	-	
$R_{\theta JA}$	结至环境热阻最大值	62.5	62.5	

封装标识与订购信息

器件标识	设备	封装	规格	带宽	数量
FDP10N60NZ	FDP10N60NZ	T0-220	-	-	50
FDPF10N60NZ	FDPF10N60NZ	T0-220F	-	-	50

电气特性 $T_c = 25^\circ\text{C}$, 除非另有说明

符号	参数	测试条件	最小值	典型值	最大值	单位
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关断特性

BV_{DSS}	漏极-源极击穿电压	$I_D = 250\ \mu\text{A}$, $V_{GS} = 0\text{V}$, $T_J = 25^\circ\text{C}$	600	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	击穿电压温度系数	$I_D = 250\ \mu\text{A}$, 推荐选用 25°C	-	0.6	-	V/ $^\circ\text{C}$
I_{DSS}	零栅极电压漏极电流	$V_{DS} = 600\text{V}$, $V_{GS} = 0\text{V}$	-	-	1	μA
		$V_{DS} = 480\text{V}$, $T_c = 125^\circ\text{C}$	-	-	10	
I_{SS}	栅极-体漏电流	$V_{GS} = \pm 25\text{V}$, $V_{DS} = 0\text{V}$	-	-	± 10	μA

导通特性

$V_{GS(th)}$	栅极阈值电压	$V_{GS} = V_{DS}$, $I_D = 250\ \mu\text{A}$	3.0	-	5.0	V
$R_{DS(on)}$	漏极至源极静态导通电阻	$V_{GS} = 10\text{V}$, $I_D = 5\text{A}$	-	0.64	0.75	Ω
g_{FS}	正向跨导	$V_{DS} = 20\text{V}$, $I_D = 5\text{A}$	-	14	-	S

动态特性

C_{iss}	直流母线电容值	$V_{DS} = 25\text{V}$, $V_{GS} = 0\text{V}$	-	1110	1475	pF
C_{oss}	输出电容	$f = 1\text{MHz}$	-	130	175	pF
C_{rss}	反向传输电容		-	10	15	pF
Q_g	10V的栅极电荷总量	$V_{DS} = 480\text{V}$, $I_D = 10\text{A}$ $V_{GS} = 10\text{V}$	-	23	30	nC
Q_{GS}	栅极-源极栅极电荷		-	6	-	nC
Q_{gd}	栅极-漏极“密勒”电荷		(说明4)	-	8	-

开关特性

$t_{d(on)}$	导通延迟时间	$V_{DD} = 300\text{V}$, $I_D = 10\text{A}$ $R_\theta = 25^\circ\text{C}$	-	25	60	ns	
t_r	开通上升时间		-	50	110	ns	
$t_{d(off)}$	关断延迟时间		(说明4)	-	70	150	ns
t_f	关断下降时间		-	50	110	ns	

漏极-源极二极管特性

I_S	漏极-源极二极管最大正向连续电流	-	-	10	A	
I_{SM}	漏极-源极二极管最大正向脉冲电流	-	-	40	A	
V_{SD}	漏极-源极二极管正向电压	$V_{GS} = 0\text{V}$, $I_{SD} = 10\text{A}$	-	-	1.4	V
t_{rr}	反向恢复时间	$V_{GS} = 0\text{V}$, $I_{SD} = 10\text{A}$ $di_F/dt = 100\text{A}/\mu\text{s}$	-	300	-	ns
Q_{rr}	反向恢复电荷		-	2	-	μC

注意:

- 重复率额定值: 脉冲宽度受限于最大结温
- $L = 11\text{mH}$, $I_{AS} = 10\text{A}$, $V_{DD} = 50\text{V}$, $R_\theta = 25^\circ\text{C}$, 开始 $T_J = 25^\circ\text{C}$
- $I_{SD} \leq 10\text{A}$, $di/dt < 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, 开始 $T_J = 25^\circ\text{C}$
- 本质上独立于操作温度的典型特性

典型性能特征

图1. 通态区域特性

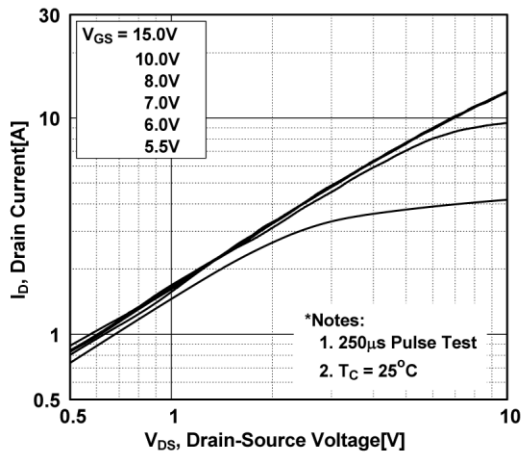


图2. 传递特性

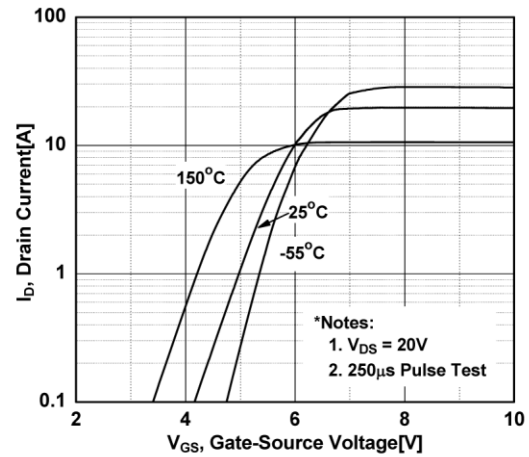


图3. 通态变化与漏极电流和栅极电压

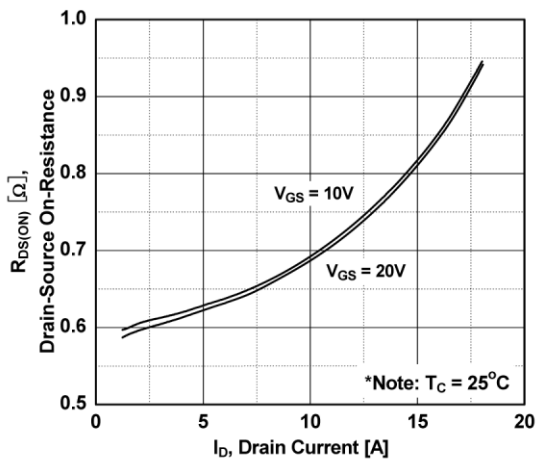


图4. 体二极管正向电压变化与源极电流和温度

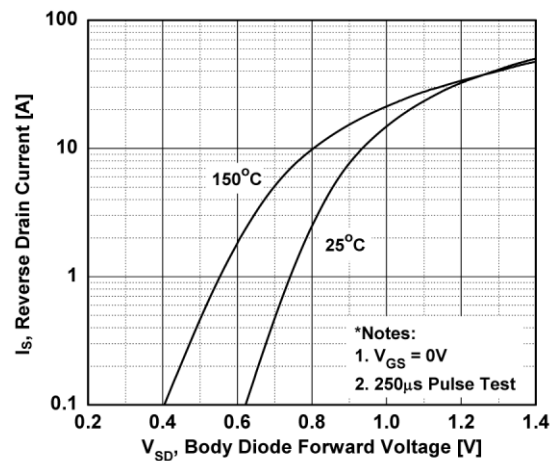


图5. 电容特性

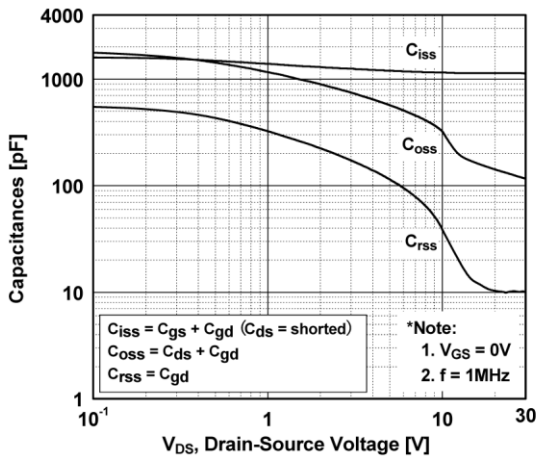
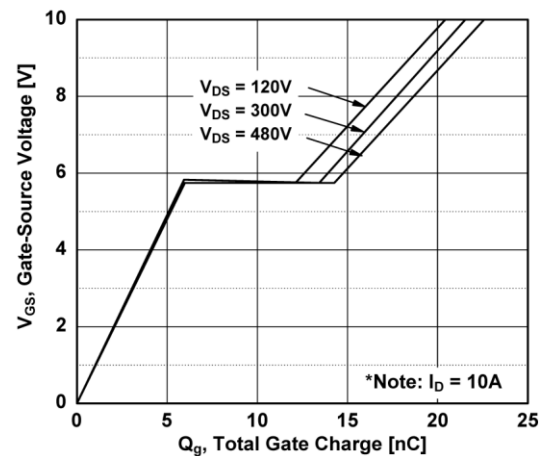


图6. 栅极电荷特性



典型性能特征 (接上页)

图7. 击穿电压变化 vs 温度

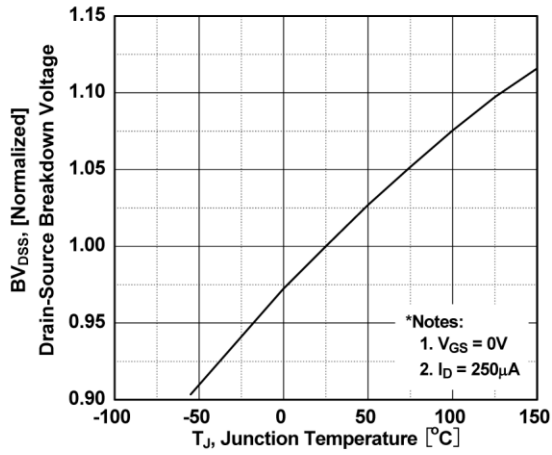


图9. 最大安全操作区 -FDP10N60NZ

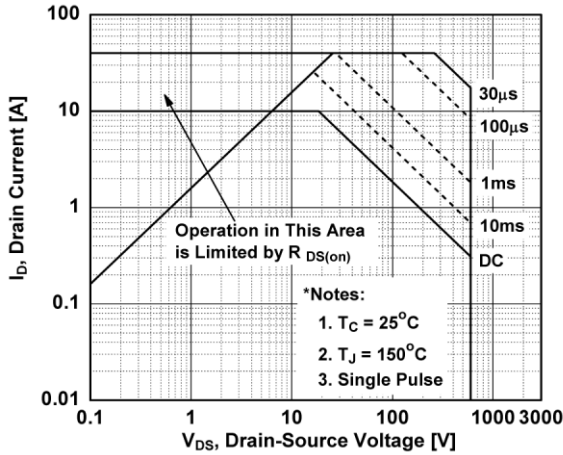


图11. 最大漏极电流与壳体温度

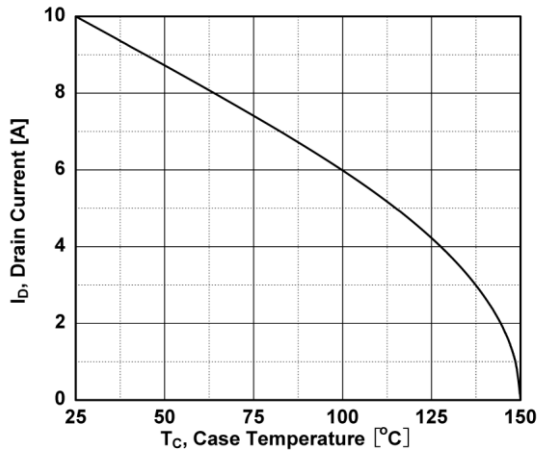


图8. 通态变化 vs 温度

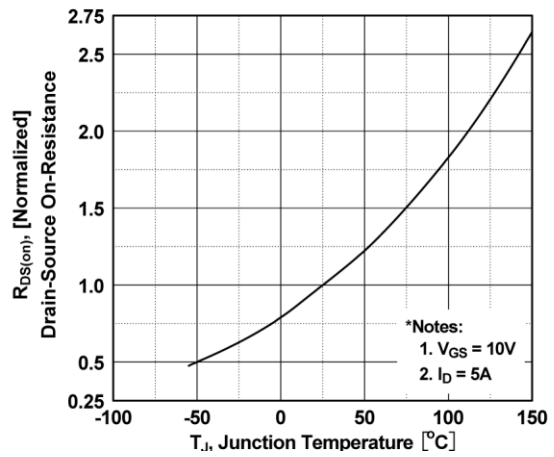


图10. 最大安全工作区 -FDP10N60NZ

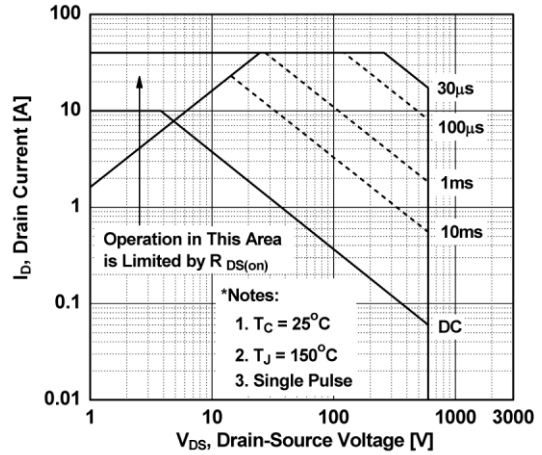


图 12. 瞬态热响应曲线 - FDP10N60NZ

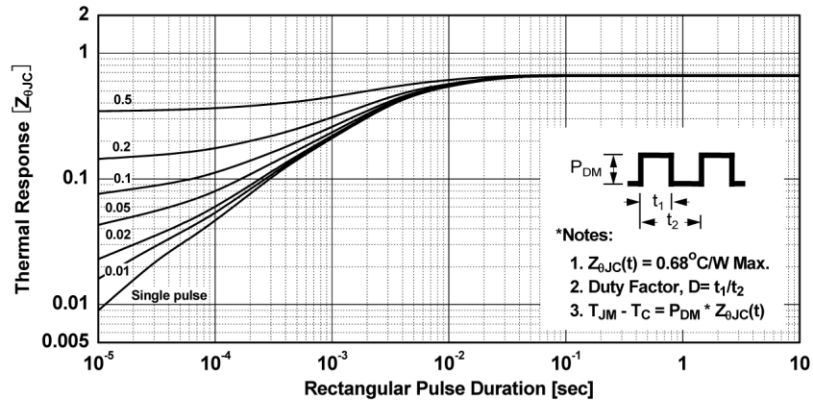
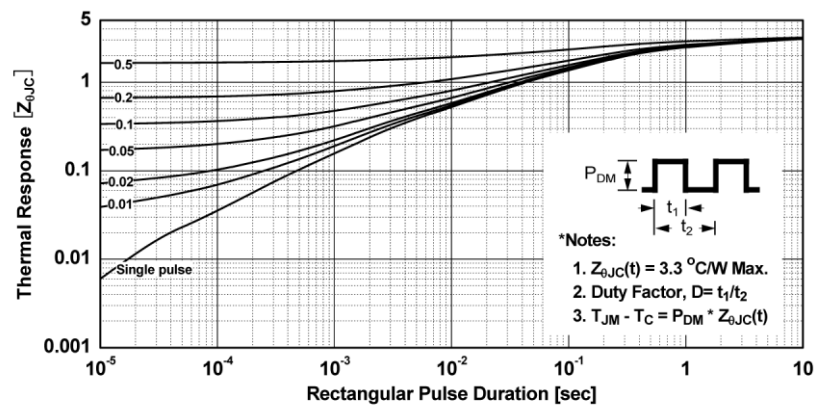
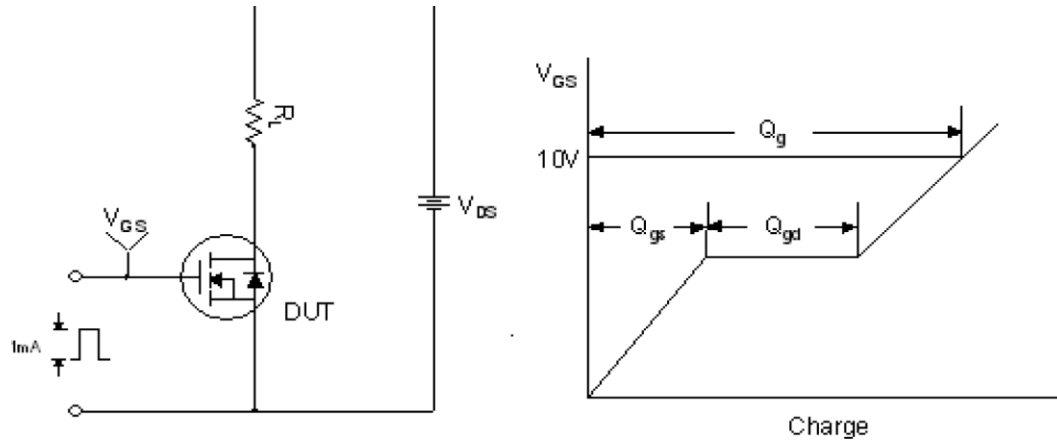


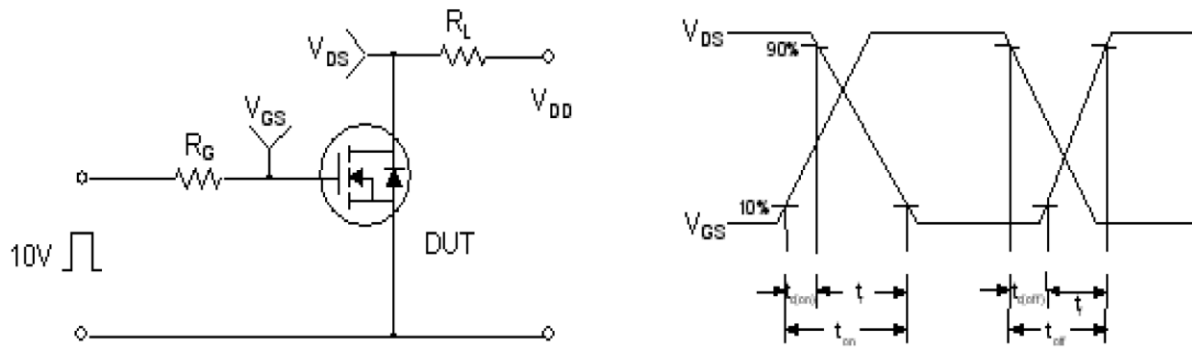
图 13. 瞬态热响应曲线 - FDPF10N60NZ



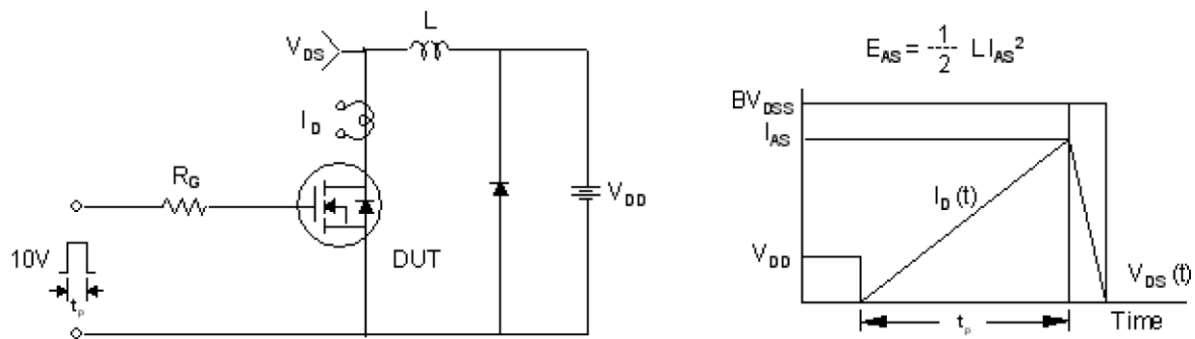
栅极电荷测试电路与波形



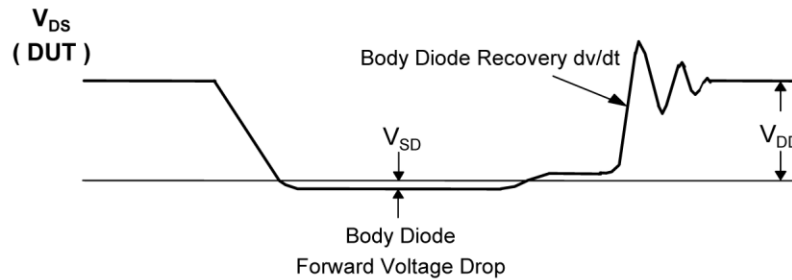
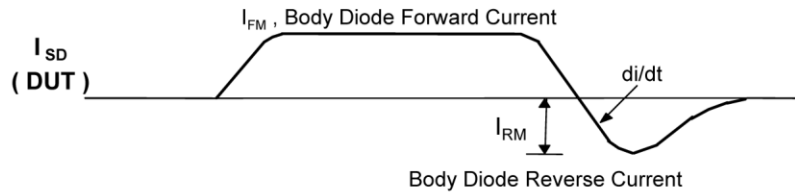
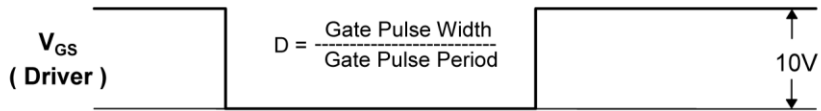
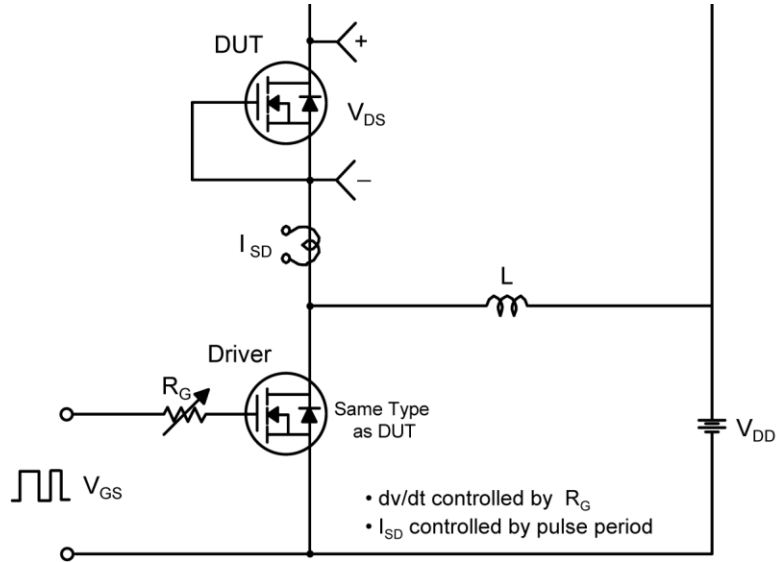
阻性开关测试电路与波形



非箝位感性开关测试电路与波形

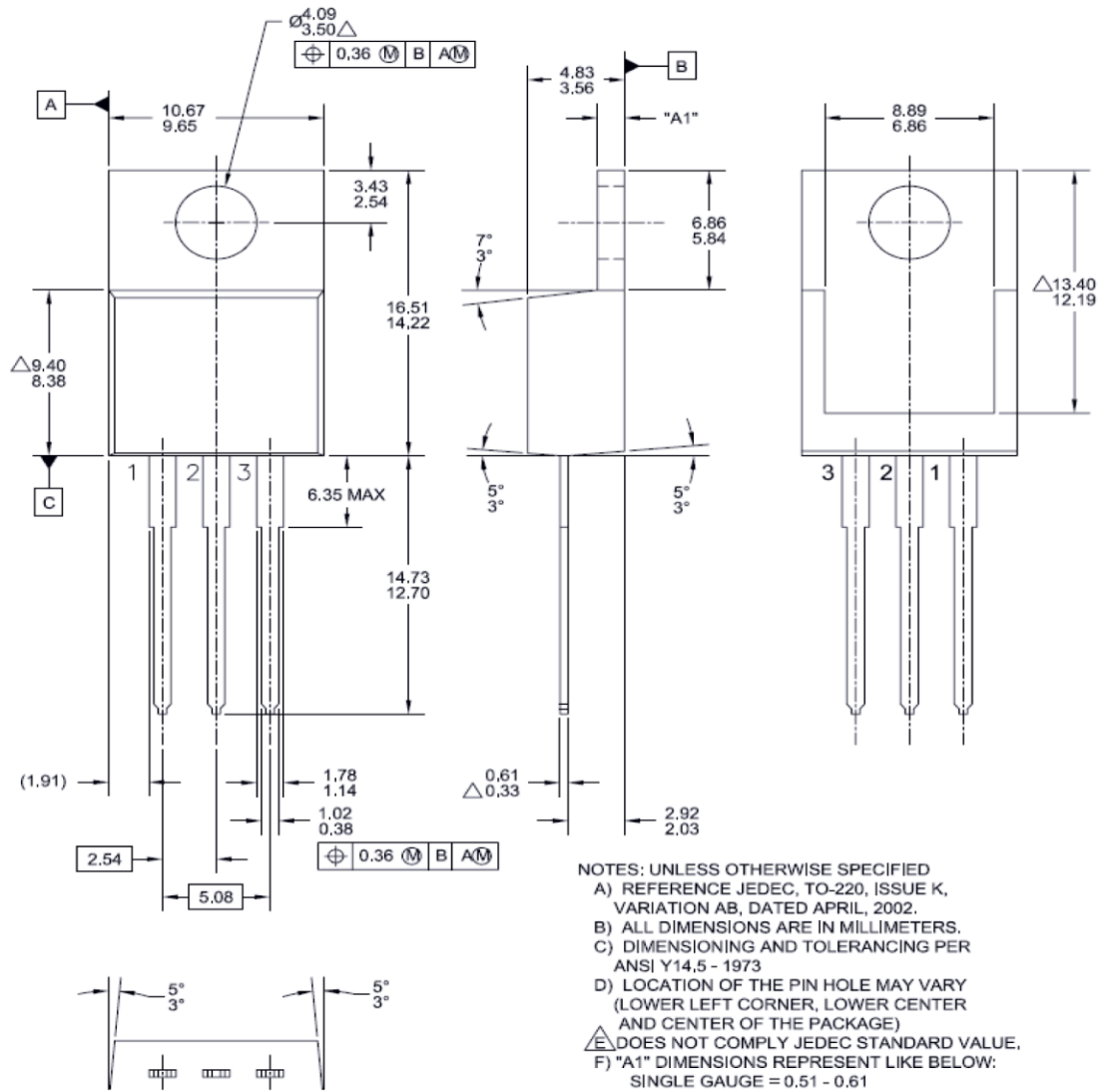


二极管恢复dv/dt峰值测试电路与波形



机械尺寸

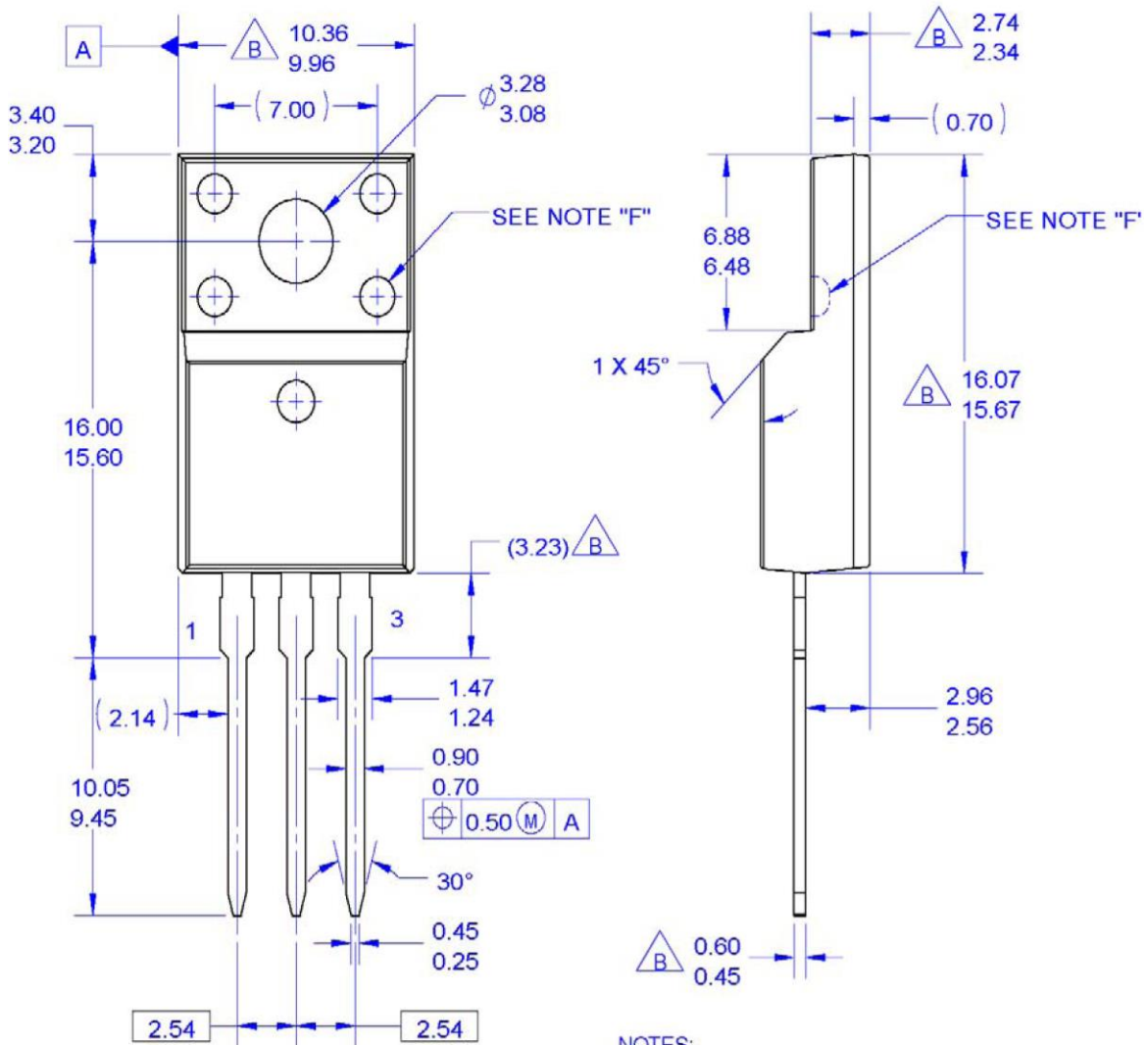
T0-220B03



尺寸单位为毫米

封装尺寸

T0-220M03




NOTES:

- A. EXCEPT WHERE NOTED CONFORMS TO EIAJ SC91A.
- B. DOES NOT COMPLY EIAJ STD. VALUE.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- E. DIMENSION AND TOLERANCE AS PER ASME Y14.5-1994.
- F. OPTION 1 - WITH SUPPORT PIN HOLE.
OPTION 2 - NO SUPPORT PIN HOLE.
- G. DRAWING FILE NAME: T0220M03REV3



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| Build it Now™ | Green Bridge™ | QS™ | TinyCalc™ |
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Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
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